

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Canceled)

2. (Currently Amended) A resist underlayer anti-reflective coating forming composition for use in a lithography process of manufacture of a semiconductor device comprising:

a polymer compound produced by addition polymerization having an epoxy group;

a compound with a molecular weight of 2000 or less having at least two carboxyl groups, or protected carboxyl groups; and

~~a solvent~~solvent,

wherein the resist underlayer anti-reflective coating forming composition contains no strong acid catalyst.

3. (Currently Amended) A resist underlayer anti-reflective coating forming composition for use in a lithography process of manufacture of a semiconductor device comprising:

an s-triazine trione skeleton compound with a molecular weight of 2000 or less having at least two epoxy groups;

a polymer compound having a phenolic hydroxyl group, a carboxyl group, a protected carboxyl group or an acid anhydride structure; and

~~a solvent~~solvent,

wherein the resist underlayer anti-reflective coating forming composition contains no strong acid catalyst.

4. (Currently Amended) A resist underlayer anti-reflective coating forming composition for use in a lithography process of manufacture of a semiconductor device comprising:

a solvent; and

a polymer compound having a carboxyl group or a protected carboxyl group, and an epoxy group-group.

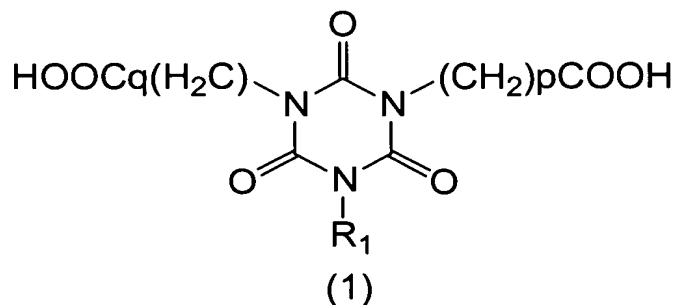
wherein the resist underlayer anti-reflective coating forming composition contains no strong acid catalyst.

5. (Previously Presented) The underlayer coating forming composition according to claim 3, wherein the polymer compound having a carboxyl group is a compound having acrylic acid or methacrylic acid as a unit structure.

6. (Previously Presented) The underlayer coating forming composition according to claim 3, wherein the polymer compound having a phenolic hydroxyl group is a compound having hydroxystyrene as a unit structure.

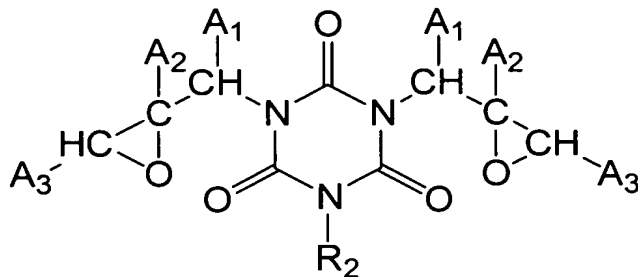
7. (Original) The underlayer coating forming composition according to claim 3, wherein the compound with a molecular weight of 2000 or less having at least two epoxy groups is a compound having at least three epoxy groups and no aromatic ring structure.

8. (Original) The underlayer coating forming composition according to claim 2, wherein the compound with a molecular weight of 2000 or less having at least two carboxyl groups is a compound of formula (1)



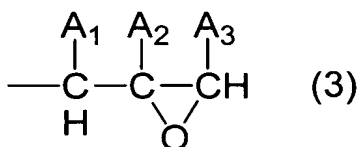
wherein p and q is a number of 1 to 6, R<sub>1</sub> is hydrogen atom, C<sub>1-6</sub> alkyl group, C<sub>3-6</sub> alkenyl group, benzyl group, phenyl group or -(CH<sub>2</sub>)<sub>r</sub>COOH wherein r is a number of 1 to 6.

9. (Original) The underlayer coating forming composition according to claim 3, wherein the compound with a molecular weight of 2000 or less having at least two epoxy groups is a compound of formula (2)



(2)

wherein A<sub>1</sub>, A<sub>2</sub> and A<sub>3</sub> each are hydrogen atom, methyl group or ethyl group, R<sub>2</sub> is hydrogen atom, C<sub>1-6</sub> alkyl group, C<sub>3-6</sub> alkenyl group, benzyl group, phenyl group or a group of formula (3)



(3)

10. (Canceled)

11. (Previously Presented) The underlayer coating forming composition according to claim 2, further comprising a light absorbing compound.

12. (Previously Presented) A method for forming an underlayer coating for use in manufacture of semiconductor device, comprising coating the underlayer coating forming composition according to claim 2.

13. (Previously Presented) A method for forming photoresist pattern for use in manufacture of semiconductor device, comprising

coating the underlayer forming composition according to claim 2 on a semiconductor substrate, and baking it to form an underlayer coating,  
forming a photoresist layer on the underlayer coating,  
exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light, and  
developing the photoresist layer after the exposure to light.

14. (Original) The method for forming photoresist pattern according to claim 13, wherein the exposure to light is carried out with a light of a wavelength of 248 nm, 193 nm or 157 nm.